DAC014N120ZZ3

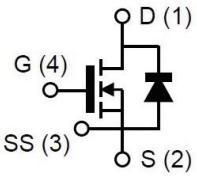
Silicon Carbide Enhancement Mode MOSFET

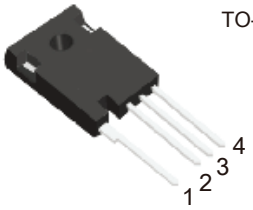
Preliminary

V_{DSS}	1200V
$I_{D(@25℃)}$	155A
$R_{DS(ON)}$	14.5mΩ

Features

- High blocking voltage with low Rds(on)
- High frequency operation with low Capacitance
- Simple to drive with -4V/+15V gate
- Robust body diode with low Qrr
- 100% Avalanche Tested





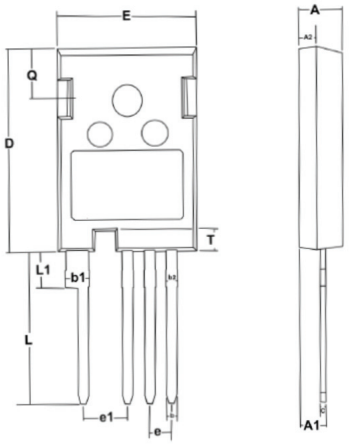
Benefits

- Superior robustness and system reliability
- Higher system efficiency
- Easier paralleling without thermal runaway
- Capable of high temperature application
- Faster and more efficient switching

Applications

- EV motor drives
- EV/HEV charging station
- Energy storage and Battery charging
- High voltage DC-DC converters
- Solar / Wind Inverters
- UPS and PFC

Package Dimensions



Symbol	Dimensions in millimeters		
	Min.	Avg.	Max.
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.80	2.00	2.20
b	1.06	1.21	1.36
b1	2.33	2.63	2.93
b2	1.07	1.30	1.60
C	0.51	0.61	0.75
D	23.30	23.45	23.60
E	15.74	15.94	16.14
e	2.54 BSC		
e1	5.08 BSC		
L	17.27	17.57	17.87
L1	3.99	4.19	4.39
Q	5.49	5.79	6.09
T	2.35	2.50	2.65

Absolute Maximum Ratings

(Tc = 25℃ unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage	V_{GS}=0V, I_D=100μA	V_{DS}	1200	V
Gate-Source Voltage		V_{GS}	-4/+15	V
Drain Current-Continuous	@ T_C =25°C @ T_C =100°C	I_D	155 110	A
Pulse Drain Current		$I_{D,pulse}$	313	A
Power Dissipation		P_D	652	W
Storage Temperature Range		T_{STG}	-55 to +175	°C
Operating Junction Temperature Range		T_J	-55 to +175	°C
Thermal Resistance, Junction-to-Case		T_L	260	°C
Avalanche Capability, single pulse *	V_{DD}=100V V_{GS}=15V L=2mH	I_{AV}	55	A
Avalanche Capability, single pulse**	V_{DD}=100V V_{GS}=15V L=2mH	E_{AV}	3025	mJ

*** 100% tested in 60% rating**
**** 100% tested in 36% rating**

Electrical Characteristics @ T_C =25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
OFF Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V，I_D=0.1mA	1200	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V，V_{DS}=1200V	-	0.5	60	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=15V，V_{DS}=0V	-	5	100	nA
ON Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}，I_D=30mA	1.8	2.5	3.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=15V，I_D=75A	-	14.5	19	mΩ
Transconductance	g_{fs}	V_{DS}=20V，I_D=75A	-	90	-	S
Internal Gate Resistance	$R_{G(int.)}$		3.8	4.3	5.3	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=1000V V_{GS}=0V V_{AC}=25mV Freq.=100kHz	-	6550	-	pF
Output Capacitance	C_{oss}		-	202	-	
Reverse Transfer Capacitance	C_{rss}		-	10	-	
C_{oss} Stored Energy	E_{oss}		-	125	-	μJ
Turn-On Switching Energy	E_{on}	V_{DD}=800V，V_{GS}=-4V/+15V I_D=75A，$R_{G(ext)}$=2.0Ω L=200μH	-	1050	-	μJ
Turn-Off Switching Energy	E_{off}		-	350	-	
Switching Characteristics						
Turn-On Delay Time	$t_{d(on)}$	V_{DS}=800V V_{GS}=-4/+15V I_D=75A $R_{G(ext)}$=2.0Ω L=200μH	-	16	-	ns
Rise Time	t_r		-	37	-	
Turn-Off Delay Time	$t_{d(off)}$		-	67	-	
Fall Time	t_f		-	13	-	
Total Gate Charge	Q_g	V_{DS}=800V V_{GS}=-4/+15V I_D=75A	-	235	-	nC
Gate to Source Charge	Q_{gs}		-	74	-	
Gate to Drain Charge	Q_{gd}		-	73	-	
Body Diode Characteristics						
Inverse Diode Forward Voltage	V_{SD}	V_{GS}=-4V，I_{SD}=40A T_J=25°C	-	4.2	-	V
Continuous Diode Forward Current	I_S	V_{GS}=-4V，T_J=25°C	-	128	-	A
Reverse Recovery Time	T_{rr}	V_{GS}=-4V I_{SD}=75A，V_{DS}=800V, dif/dt=2400A/μs T_J=25°C	-	25	-	ns
Reverse Recovery Charge	Q_{rr}		-	670	-	nC
Peak Reverse Recovery Current	I_{rrm}		-	45	-	A
Thermal Resistance						
Thermal Resistance, Junction-to-Case	$R\theta_{JC}$		-	0.21	0.23	°C/W

Typical Performance

Fig 1. Output Characteristics, T_J = -40°C

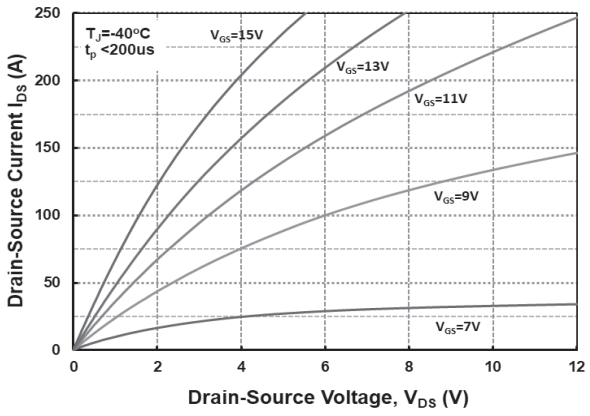


Fig 2. Output Characteristics, T_J = 25°C

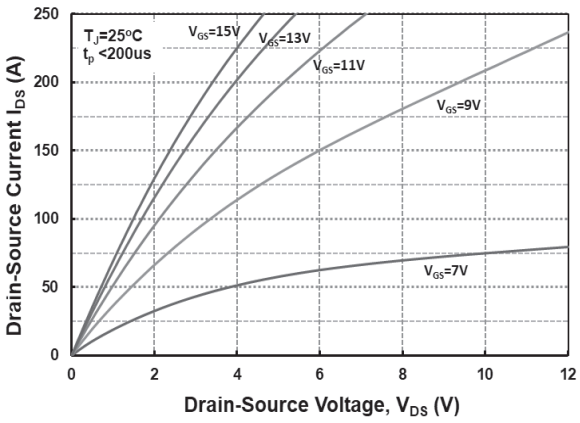


Fig 3. Output Characteristics, T_J = 175°C

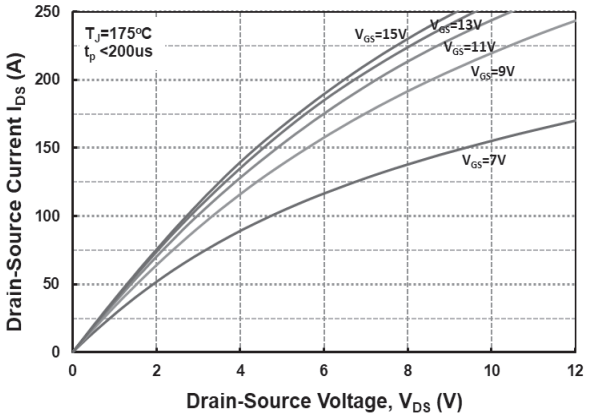


Fig 4. Normalized On-Resistance vs. Temperature

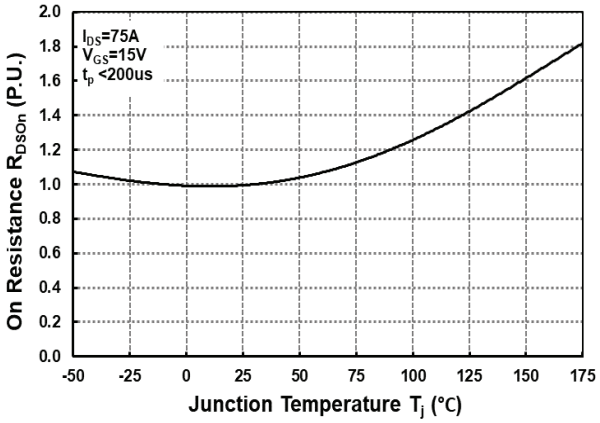


Fig 5. On-Resistance vs. Drain Current for Various Temperatures

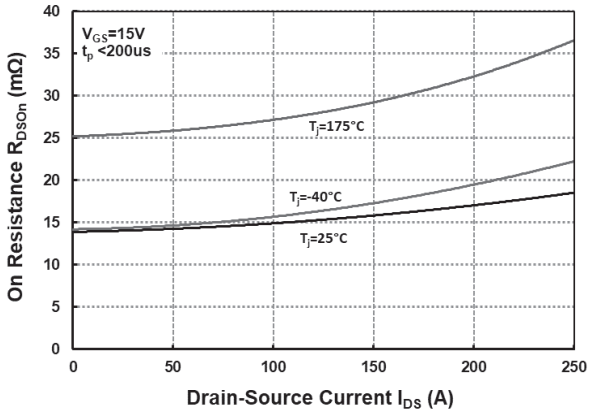
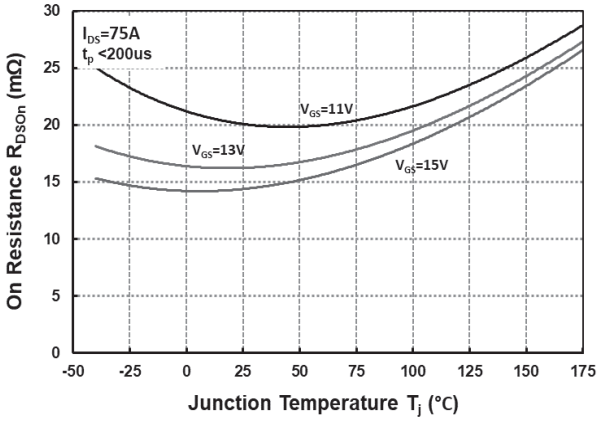


Fig 6. On-Resistance vs. Temperature for Various Gate Voltage



Typical Performance

Fig 7. Transfer Characteristic for Various Junction Temperatures

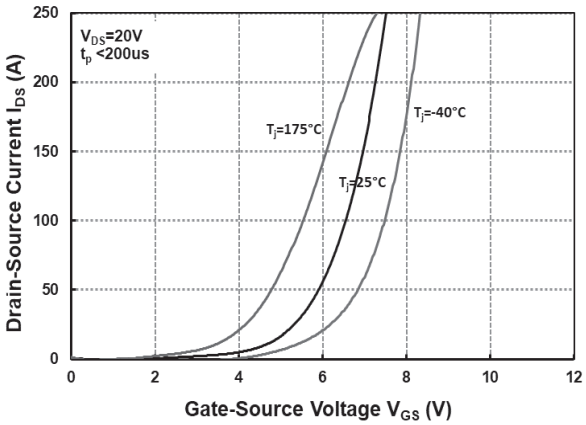


Fig 8.Body Diode Characteristics @ -40°C

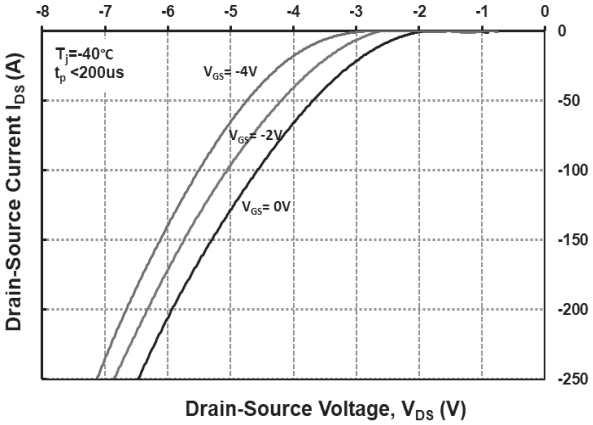


Fig 9. Body Diode Characteristics @ 25°C

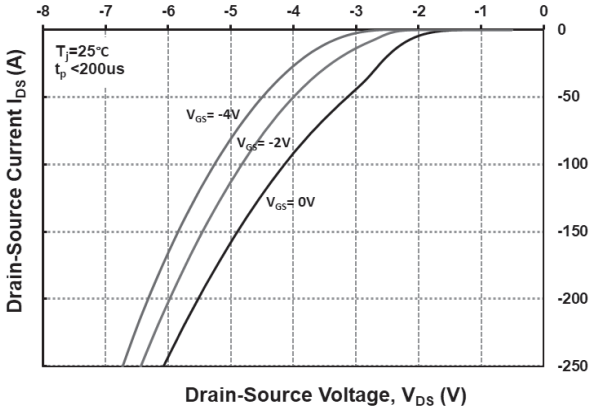


Fig 10. Body Diode Characteristics @ 175°C

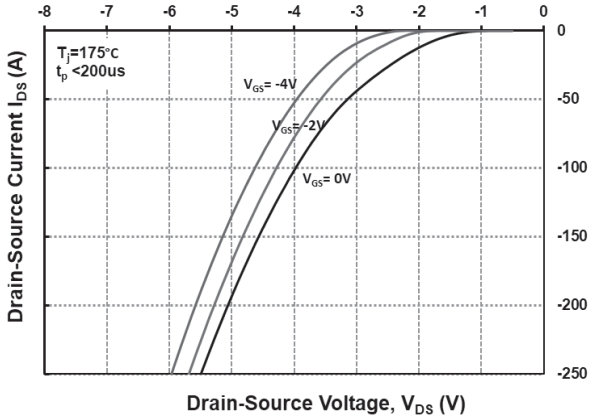


Fig 11. Threshold Voltage vs. Temperature

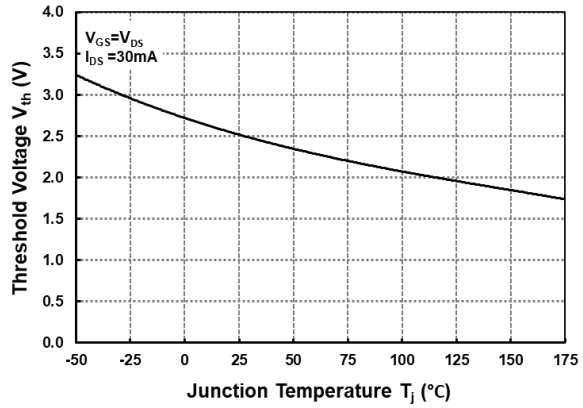
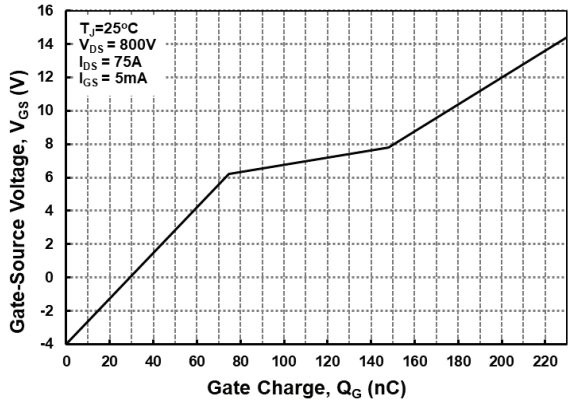


Fig 12. Gate Charge Characteristics



Typical Performance

Fig 13. 3rd Quadrant Characteristics @ -40°C

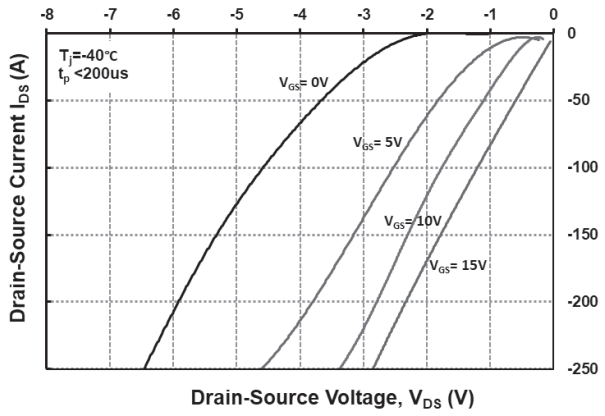


Fig 14. 3rd Quadrant Characteristics @ 25°C

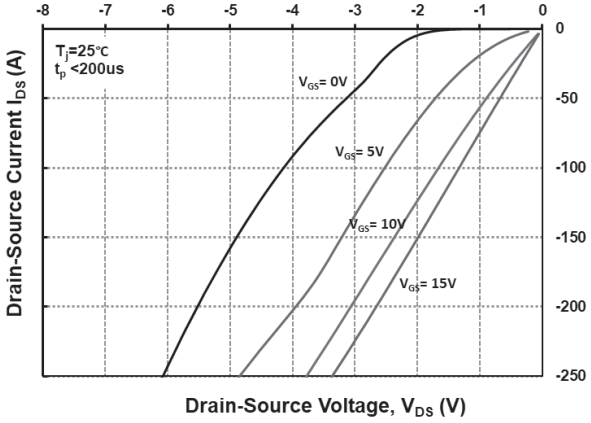


Fig 15. 3rd Quadrant Characteristics @ 175°C

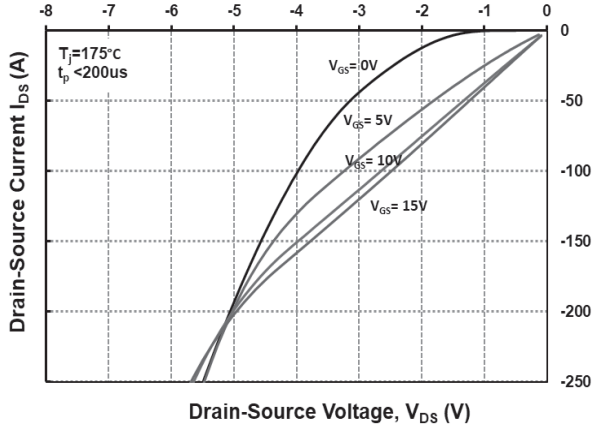


Fig 16. Output Capacitor Stored Energy

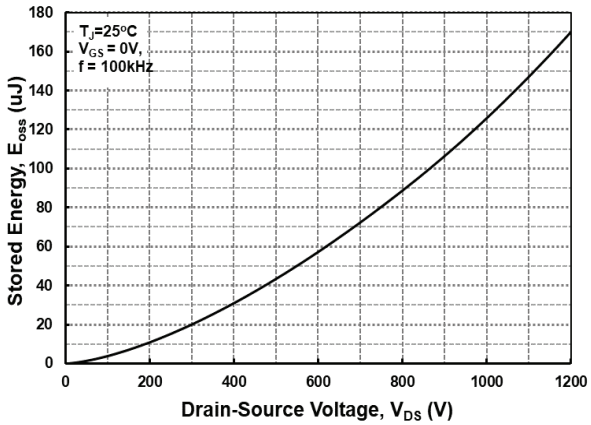


Fig 17. Capacitances vs. Drain-Source Voltage (0-200V)

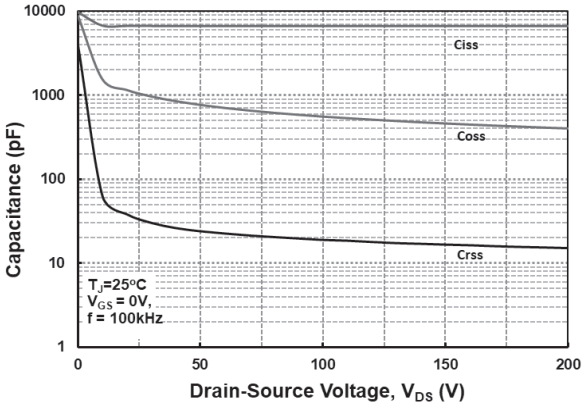
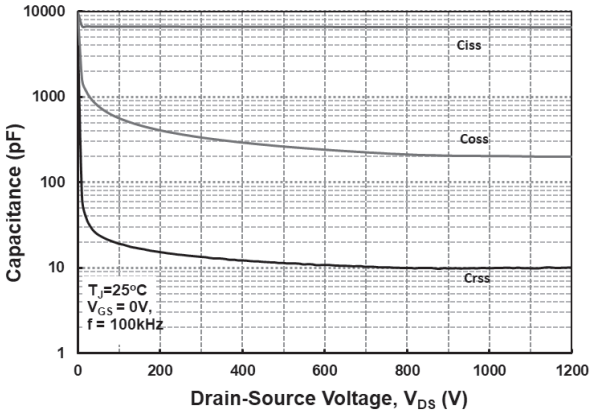


Fig 18. Capacitances vs. Drain-Source Voltage (0-1200V)



Typical Performance

Fig 19. Continuous Drain Current Derating vs. Case Temperature

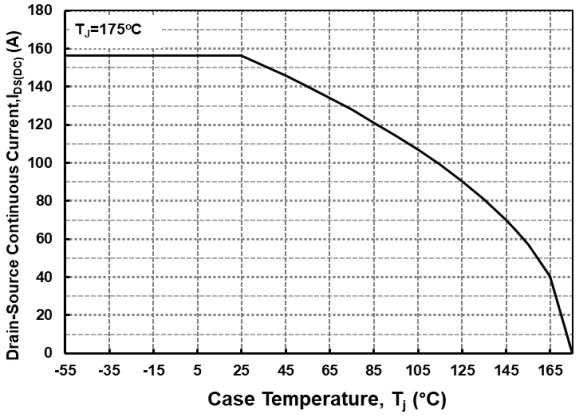


Fig 20. Maximum Power Dissipation Derating vs. Case Temperature

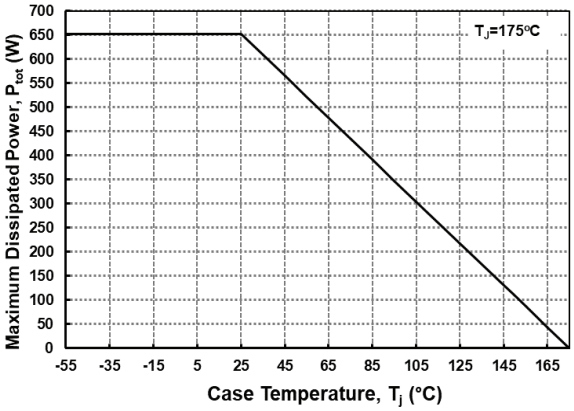


Fig 21. Transient Thermal Impedance (Junction – Case)

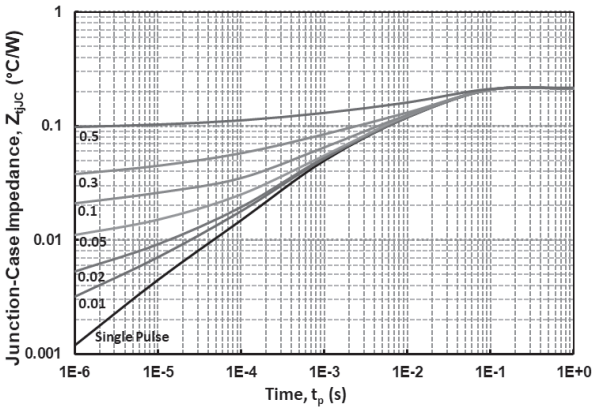


Fig 22. Safe Operating Area

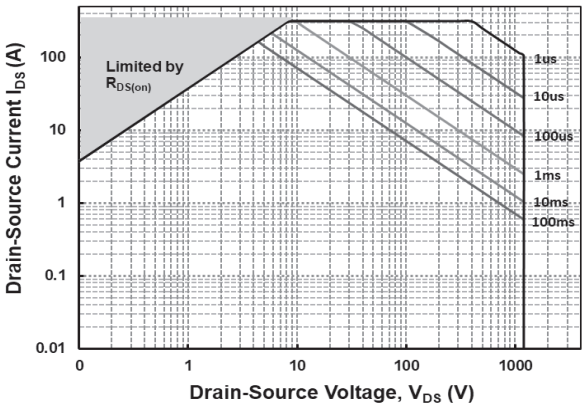


Fig 23. Clamped Inductive Switching Energy vs Drain Current (V_{DD} = 800V)

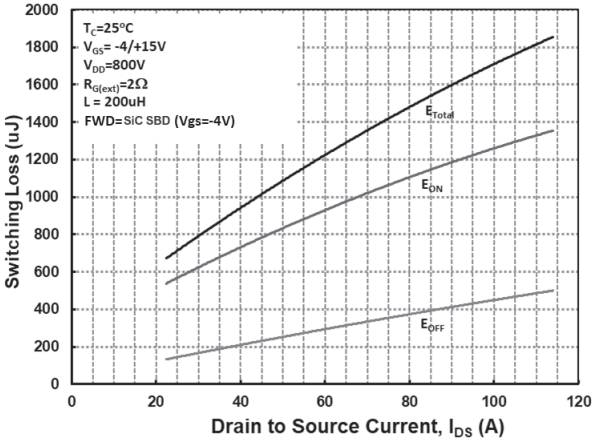
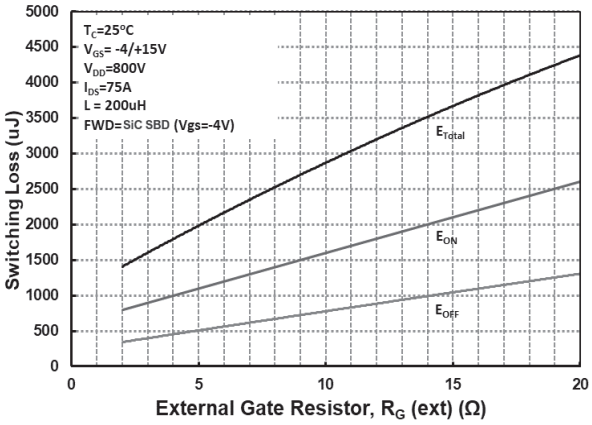


Fig 24. Clamped Inductive Switching Energy vs External Gate Resistor $R_{G(ext)}$



Typical Performance

Fig 25. Switching Times vs Drain Current (V_{DD} = 800V)

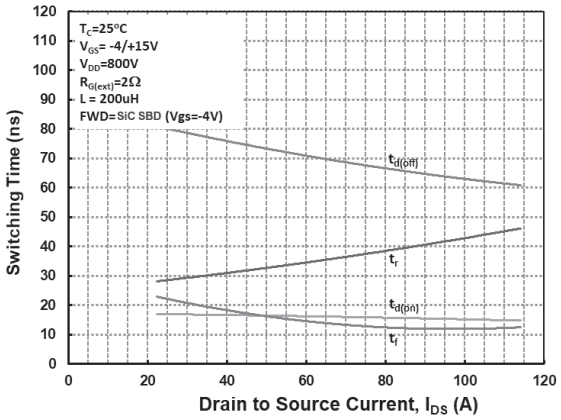
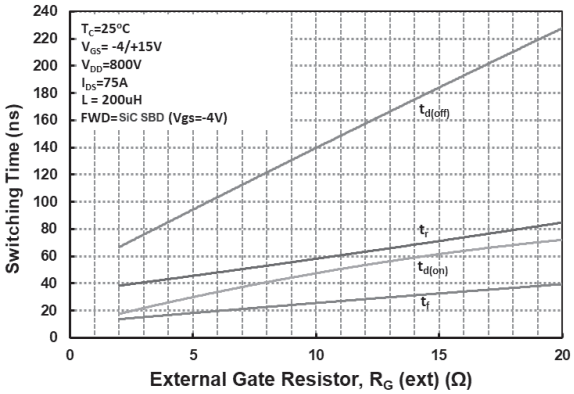


Fig 26. Switching Times vs External Gate Resistor $R_{G(ext)}$



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